



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

RECEIVED
JAN 21 2003
TECHNOLOGY CENTER 2800

In re Application of

Sawazaki, et al.

Serial No.: 09/522,832

Group Art Unit: 2815

Filed: March 10, 2000

Examiner: Baumeister, B.

For: GROUP III NITRIDE COMPOUND SEMICONDUCTOR LIGHT-EMITTING
DEVICE

#25/D
Amdt.
J. McInulla
2/3/03

Honorable Assistant Commissioner of Patents
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Sir:

Prior to evaluation on the merits, please amend the above-identified Application as follows:

IN THE CLAIMS:

Please revise the claims to read as follows.

SUB
E1
DI

1. (Three Times Amended) A group III nitride compound semiconductor light-emitting device, comprising:

a light-emitting layer of a multilayer quantum well structure composed of alternately laminated well layers and barrier layers; and

an n-type clad layer being in contact with said light-emitting layer,
wherein said n-type clad layer is made thicker than each of said barrier layers and the thickness of said n-type clad layer is in a range of 100 Å to 500 Å, and

wherein said n-type clad layer is formed of a material substantially the same as said barrier layers, thereby providing a band gap in said n-type clad layer that is substantially the same as a band gap in said barrier layers.

Please add the following new claims: